



Study of Thermoelectric Effect Using a Peltier Module

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ABSTRACT:

This study investigates the performance characteristics and thermodynamic limitations of a TEC1-12706 thermoelectric cooler (Peltier module) through experimental analysis. The research validates the governing equations of thermoelectricity, specifically exploring the relationship between electrical power input and the achieved temperature gradient (ΔT). By utilizing a controlled "thermal stack" assembly, the study evaluates the performance of the module under varying current levels and assesses the critical impact of thermal management on overall cooling efficiency. The findings demonstrate that while the Peltier effect provides a reliable, solid-state solution for localized cooling, the system is fundamentally constrained by the quadratic increase in Joule heating and the efficiency of heat rejection at the hot junction. The experimental results align with theoretical predictions, identifying an optimal operating current that maximizes the coefficient of performance (CoP) before the onset of thermal saturation.

KEYWORDS: Peltier Effect, Seebeck Effect, Figure of Merit (ZT), Joule Heating, TEC1-12706 Bismuth Telluride, Phonon-Glass Electron-Crystal (PGEC), Thermal Gradient, Thermal Back-Conduction, Coefficient of Performance (CoP), Thermal Saturation, Thermal Interface Material (TIM), Thermal Stack, Doping.

I. INTRODUCTION:

1.1 Background of the Study: The quest for efficient, solid-state energy conversion technologies has become a cornerstone of modern materials science and engineering. As the global demand for sustainable energy solutions and precise temperature control grows, thermoelectric devices—specifically Peltier modules—have emerged as a vital technology. Thermoelectricity refers to the direct conversion of temperature differences to electric voltage (the Seebeck effect) and the direct conversion of electric current to temperature differences (the Peltier effect).

A Peltier module, or Thermoelectric Cooler (TEC), is a solid-state active heat pump that transfers heat from one side of the device to the other when an electric current is passed through it. Unlike traditional refrigeration systems that rely on mechanical compressors, chemical refrigerants (such as chlorofluorocarbons), and moving parts, Peltier modules operate purely through electronic phenomena at the semiconductor junction level. This unique characteristic makes them silent, vibration-free, highly reliable, and environmentally friendly, as they do not contribute to the depletion of the ozone layer or the production of greenhouse gases associated with conventional refrigeration cycles.



The history of thermoelectricity dates back to the 19th century with the discovery of the Seebeck effect in 1821 by Thomas Johann Seebeck and the subsequent discovery of the Peltier effect in 1834 by Jean Charles Athanase Peltier. However, it was not until the development of modern semiconductor physics in the mid-20th century, specifically the utilization of bismuth telluride (Bi_2Te_3) alloys, that these effects became technologically and commercially viable. Today, Peltier modules are ubiquitous, found in everything from small-scale applications like cooling CPU microprocessors and portable beverage coolers to specialized laboratory equipment like laser diode temperature controllers and medical diagnostic devices.

1.2 Problem Statement: Despite the clear advantages of thermoelectric cooling—such as compactness, high reliability, and precise temperature control—their widespread adoption in large-scale cooling applications is limited by relatively low energy efficiency. The Coefficient of Performance (COP) of standard Peltier modules remains significantly lower than that of conventional vapor-compression refrigeration systems.

Furthermore, the performance of a Peltier module is highly sensitive to the thermal management of its "hot" side. In many practical applications, the inability to effectively dissipate heat away from the hot side leads to back-conduction, which rapidly degrades the cooling efficiency and can even lead to thermal runaway and permanent damage to the module. Therefore, there is a critical need to experimentally quantify the relationship between electrical input and thermal gradient, understand the impact of thermal load, and identify the limitations inherent in these solid-state devices. This project seeks to bridge the gap between theoretical semiconductor physics and practical experimental performance.

1.3 Objectives of the Study: The primary objective of this research project is to conduct a comprehensive study of the thermoelectric effect using a Peltier module. To achieve this, the following specific objectives have been established:

- **To experimentally characterize the Peltier effect:** To measure the temperature difference (ΔT) across the module as a function of the applied electrical input (voltage and current).
- **To evaluate thermal performance:** To investigate how the rate of heat transfer is affected by variations in current, and to determine the point of maximum cooling efficiency.
- **To analyze the impact of heat dissipation:** To assess the importance of effective heat sinking on the hot side and demonstrate the consequences of insufficient thermal management.
- **To validate theoretical models:** To compare experimental results against standard thermoelectric equations, such as the relationship governed by the Figure of Merit (ZT).
- **To demonstrate practical applications:** To provide a clear, evidence-based demonstration of how Peltier modules function for cooling purposes, offering insights into their limitations and potential for future technological integration.

1.4 Scope and Limitations: The scope of this study is limited to the investigation of a single-stage, standard commercial Peltier module. The research will focus on the steady-state performance of the device under controlled laboratory conditions. It will not involve the development of new thermoelectric materials or the optimization of the semiconductor doping levels.

The experimental setup will utilize standard heat sinks and fan cooling systems to manage the heat flux on the hot side. While this provides a realistic representation of common usage, it is acknowledged that the results may vary depending on the specific thermal resistance of the interfaces and the efficiency of the heat dissipation components used. Furthermore, the study will focus primarily on the Peltier effect (cooling mode) and may briefly touch upon the Seebeck effect (power generation mode) only insofar as it informs the overall understanding of the thermoelectric module's physics.



1.5 Significance of the Study: This research is significant because it provides a foundational understanding of an increasingly relevant technology in an era where energy efficiency and green cooling technologies are prioritized. By documenting the performance of a Peltier module, this study serves as a reference for students, engineers, and researchers interested in small-scale thermal management.

Beyond the academic exercise, the insights gained regarding thermal resistance and current-to-cooling ratios have direct applications in the design of cooling systems for high-performance electronics, where precise temperature maintenance is critical for longevity and stability. As we move toward more sustainable cooling solutions, understanding the fundamental physics of thermoelectric devices provides the necessary basis for future innovations in solid-state climate control.

CHAPTER 2: THEORETICAL FRAMEWORK

2.1 The Physics of Thermoelectricity: An In-Depth Analysis: The thermoelectric effect represents a fascinating intersection of solid-state physics, thermodynamics, and charge carrier dynamics. At its most fundamental level, it describes the interconversion of thermal energy—the random, microscopic kinetic energy of atoms and electrons—and electrical energy, which is the directed flow of charge. Unlike mechanical heat engines, which rely on moving pistons or turbines to convert heat into work, thermoelectric devices operate entirely through the interaction between charge carriers and the crystal lattice of a material.

2.1.1 Charge Carrier Dynamics and Entropy: To understand thermoelectricity, one must consider the behavior of charge carriers—electrons (in n-type materials) and holes (in p-type materials)—within a solid. These carriers possess both charge and energy. When a temperature gradient is applied across a conductor, the carriers at the "hot" end gain higher average kinetic energy compared to those at the "cold" end.

Due to this energy distribution, carriers naturally tend to diffuse from the hot region to the cold region. As they migrate, they carry their energy with them. In an open-circuit configuration, this migration leads to an accumulation of charge at the cold end and a depletion at the hot end, creating an internal electric field that eventually opposes further diffusion. This equilibrium state is what we measure as the Seebeck voltage.

The "efficiency" of this carrier transport is heavily dependent on the material's electronic band structure. In metals, electrons have high mobility, but they are so numerous and move so quickly that the Seebeck effect is generally very small. In insulators, electrical conductivity is too low to facilitate a meaningful current. Therefore, semiconductors—specifically those with a narrow bandgap—are the ideal medium, as they allow for a controlled concentration of charge carriers that can be manipulated by doping.

2.1.2 The Role of Phonons and Scattering: The movement of charge carriers is not uninterrupted. As they travel through the crystal lattice, they collide with atomic vibrations (phonons) and impurities. These scattering events are critical in the study of thermoelectricity for two main reasons:

1. **Energy Filtering:** If a material is engineered (often through nanostructuring) to preferentially scatter low-energy carriers while allowing high-energy carriers to pass, the average energy per charge carrier increases, which significantly boosts the Seebeck coefficient (α).

2. **Thermal Conductivity Paradox:** The fundamental challenge in thermoelectric physics is the "Wiedemann-Franz Law," which states that a material that conducts electricity well will also conduct heat well. This is because both heat and charge are carried by the same electrons. A perfect thermoelectric material must possess high electrical conductivity (σ) to minimize resistive (Joule) heating, but very low thermal conductivity (κ) to prevent the heat from simply flowing back across the gradient.



2.1.3 Thermodynamic Reversibility: A defining characteristic of thermoelectric phenomena is their inherent thermodynamic reversibility. Because these effects are governed by the linear relationship between fluxes (heat flux and charge flux) and forces (temperature gradient and electric potential gradient), a Peltier module can be seamlessly switched between roles.

In the Peltier mode, we apply an electric potential to force entropy to be carried away from the cold junction, essentially acting as an electron-based heat pump. In the Seebeck mode, we apply a temperature gradient to "push" the charge carriers, turning the device into an electron-based heat engine.

This reversibility is described by the Onsager Reciprocal Relations, which provide the mathematical foundation for why the Seebeck coefficient (α) and the Peltier coefficient (π) are strictly related by the absolute temperature (T) through the relation $\pi = \alpha T$. This relationship is not merely a coincidence but a manifestation of the underlying time-reversal symmetry of the microscopic physical laws governing electron-phonon interactions.

2.1.4 Summary of the Energy Landscape: In summary, the thermoelectric effect is a manifestation of how entropy is transported through a material. When we power a Peltier module, we are essentially using the electric field to exert a force on the charge carriers that overcomes the natural diffusive tendency to distribute heat evenly. By "sweeping" the carriers in one direction, we force the hot junction to dump heat into the surroundings while simultaneously "clearing" the cold junction of its thermal energy. This is a purely electronic process that requires no phase changes or mechanical work, positioning it as one of the most elegant, albeit challenging, methods of energy conversion in physics today.

2.2 The Seebeck Effect: The Foundation of Thermoelectric Power, The Seebeck effect, named after the German physicist Thomas Johann Seebeck who discovered it in 1821, is the foundational phenomenon behind thermoelectric power generation. It describes the process by which a temperature gradient across a conductive or semiconducting material is directly converted into an electromotive force (EMF), or voltage.

2.2.1 The Microscopic Mechanism: Diffusion and Phonon Drag: At the atomic level, the Seebeck effect is driven by the tendency of charge carriers—electrons in n-type materials and holes in p-type materials—to diffuse from regions of high thermal energy to regions of low thermal energy.

1. **Carrier Diffusion:** In a conductor subjected to a temperature gradient, carriers at the hot junction possess higher average kinetic energy due to the Boltzmann distribution. These "hot" carriers diffuse toward the colder end of the material. As they migrate, they leave behind a net charge imbalance at the hot end and create a corresponding accumulation at the cold end. This separation of charge establishes an internal electric field that exerts a force opposing further diffusion. When the force from the electric field exactly balances the diffusive force driven by the temperature gradient, a steady-state open-circuit voltage is achieved.

2. **Phonon Drag:** Beyond simple carrier diffusion, there is a secondary contribution known as "phonon drag." When a temperature gradient exists, a flux of phonons (lattice vibrations) moves from the hot side to the cold side. As these phonons travel, they frequently collide with electrons. These collisions impart momentum to the electrons, effectively "pushing" them toward the cold end. This phenomenon can significantly enhance the Seebeck coefficient, particularly at low temperatures, and is a vital consideration in the design of high-performance thermoelectric generators.

2.2.2 The Seebeck Coefficient (α): The magnitude of the Seebeck effect is quantified by the Seebeck coefficient, α , which is defined as:

$$\alpha = \frac{dV}{dT}$$

Where dV is the voltage generated in response to a temperature differential dT . A material with a large α is highly desirable for thermoelectric applications because it produces more voltage for a given temperature difference.

It is important to note that α is a material property that depends on the carrier concentration and the density of states near the Fermi level. For metals, the Seebeck coefficient is typically very low (on the order of microvolts per Kelvin, $\mu\text{V/K}$), because their high carrier concentration effectively "screens" the charge separation. In



contrast, semiconductors can be doped to optimize their carrier density, leading to much higher Seebeck coefficients, often ranging from 100 to 300 $\mu\text{V/K}$.

2.2.3 Practical Application: The Thermocouple: The most common application of the Seebeck effect is the thermocouple, a device consisting of two dissimilar conductors joined at one end. When the two free ends are connected to a high-impedance voltmeter, the device measures the potential difference generated by the temperature difference between the junction and the reference ends.

In a modern thermoelectric module, this principle is scaled up by connecting many p-n semiconductor pairs in electrical series. Because n-type materials develop a negative voltage at the hot end and p-type materials develop a positive voltage at the hot end, connecting them in series allows their individual voltages to sum up, resulting in a significantly larger total output voltage.

2.2.4 Linearity and Thermodynamic Constraints: Within a moderate temperature range, the Seebeck voltage is generally linear with respect to the temperature difference. However, α itself is temperature-dependent. This means that for large temperature gradients, the total voltage V is expressed by the integral:

$$V = \int_{T_c}^{T_h} \alpha(T) dT$$

This dependence requires precise material selection. For a thermoelectric device to be efficient, the chosen materials must maintain a high Seebeck coefficient across the entire operating temperature range. The study of the Seebeck effect is therefore not just about observing a voltage; it is about engineering the electronic band structure of materials to ensure that the "thermoelectric power" remains robust under real-world thermal conditions.

2.3 The Peltier Effect: Solid-State Heat Pumping: The Peltier effect is the physical phenomenon that enables solid-state cooling. Discovered by Jean Charles Athanase Peltier in 1834, it represents the inverse of the Seebeck effect: whereas the Seebeck effect converts a temperature gradient into electrical energy, the Peltier effect utilizes electrical energy to force a temperature gradient. In the context of a thermoelectric module, this effect is harnessed to "pump" heat from a cold reservoir to a hot reservoir, effectively creating a refrigerator without the need for mechanical compressors, moving parts, or liquid refrigerants.

2.3.1 The Microscopic Mechanism: Entropy Transport: To understand the Peltier effect, one must view it as the transport of entropy by charge carriers. In a semiconductor, electrons (in n-type) or holes (in p-type) are the primary carriers of both electricity and thermal energy.

When an electric current I is passed across a junction between two dissimilar materials, the charge carriers must transition between different energy states. If a carrier moves from a material where it has lower potential energy to one where it has higher potential energy, it must absorb energy from its surroundings to make the transition. Conversely, if it moves from a higher-potential state to a lower-potential state, it must release that excess energy to the surroundings.

In a Peltier module, this is engineered by alternating n-type and p-type semiconductor elements. At the cold junction, the electrons and holes move into a higher energy state, absorbing thermal energy from the junction (creating cooling). As these carriers move through the module to the hot junction, they carry this energy with them. Upon reaching the hot junction, they transition back to a lower energy state, releasing the previously absorbed heat into the hot-side heat sink. Thus, the electric current acts as a "conveyor belt" for heat, constantly moving thermal energy from the cold side to the hot side.

2.3.2 The Peltier Coefficient (π): The Peltier effect is quantified by the Peltier coefficient, π . It is defined as the heat absorbed or evolved at a junction per unit current. Crucially, the Peltier coefficient is linked to the Seebeck coefficient (α) and the absolute temperature (T) by the relation:

$$\pi = \alpha T$$



This elegant relationship is a consequence of the Kelvin Relations, which emerge from the laws of thermodynamics. It implies that materials with a higher Seebeck coefficient—which are better at converting temperature into electricity—are inherently more effective at pumping heat when an external current is applied. This is why Bismuth Telluride (Bi_2Te_3), which possesses an exceptionally high Seebeck coefficient, remains the gold standard for thermoelectric cooling applications.

2.3.3 The Role of Joule Heating and Thermal Conduction: While the Peltier effect is the desired mechanism for cooling, a real-world module is subject to parasitic effects that diminish its efficiency. When current I flows through the module, it encounters electrical resistance R , resulting in Joule heating (or Ohmic heating) described by I^2R . This heat is generated throughout the entire volume of the module. Unlike the Peltier effect, which is directional (absorbing heat at one junction and releasing it at the other), Joule heating is strictly dissipative and adds to the heat load on both sides of the module.

Simultaneously, the temperature gradient created by the cooling effect induces a back-flow of heat through the module via thermal conduction, governed by Fourier's Law ($Q_{\text{cond}} = K\Delta T$). These two factors—Joule heating and thermal conduction—are the primary adversaries of efficient thermoelectric cooling.

2.3.4 Operational Optimization: The total heat flux Q_c removed from the cold side is the net sum of the Peltier cooling, the Joule heating, and the thermal conduction:

$$Q_c = \pi I - \frac{1}{2} I^2 R - K \Delta T$$

This equation reveals the fundamental trade-offs in using a Peltier module. At low current, the Peltier cooling is insufficient. As current increases, cooling performance improves, but Joule heating increases quadratically. Eventually, the $I^2 R$ term grows faster than the Peltier term, causing a decrease in cooling capacity. There exists, therefore, an "optimal current" for any given operating condition that maximizes cooling.

The Peltier effect is not merely about achieving the lowest possible temperature, but about balancing these competing thermodynamic forces. In practical applications, the hot side must be kept at a low temperature to minimize the $K\Delta T$ (back-conduction) term, which is why robust, active heat sinking on the hot side is the most vital engineering requirement for any thermoelectric cooling system. By managing these energy flows, the Peltier effect provides a sophisticated, vibration-free, and highly precise method for thermal control in sensitive electronic and medical equipment.

2.4 The Thomson Effect and the Figure of Merit: The previous sections established the Seebeck and Peltier effects as the primary mechanisms of thermoelectricity. However, a complete thermodynamic description of a thermoelectric system requires the inclusion of the Thomson effect, and a complete evaluation of material performance requires the Figure of Merit.

2.4.1 The Thomson Effect: The Thomson effect, discovered by William Thomson (Lord Kelvin) in 1851, provides the link between the Seebeck and Peltier effects. It describes the heat absorbed or evolved by a single conductor when an electric current flows through it in the presence of a temperature gradient.

Unlike the Peltier effect, which occurs at the junction of two different materials, the Thomson effect occurs within a homogeneous material. If a current I flows along a wire with a temperature gradient dT/dx , the heat generated or absorbed per unit volume is:

$$Q_{\text{Thomson}} = -\tau I \frac{dT}{dx}$$

where τ is the Thomson coefficient.

The sign of the Thomson effect depends on the direction of the current relative to the temperature gradient. If the current flows in the same direction as the heat flow (from hot to cold), heat is absorbed or evolved depending on the material's properties. This effect is crucial for thermodynamic consistency; it accounts for the fact that the Seebeck and Peltier coefficients are not constants but vary with temperature. The relationship is governed by the second Kelvin relation:

$$\tau = T \frac{d\alpha}{dT}$$



While the Thomson effect is often small in magnitude compared to Peltier heat, it is conceptually vital. It demonstrates that the Seebeck and Peltier effects are inextricably linked through the temperature dependence of the thermoelectric properties of a material. In professional-grade simulation models of Peltier modules, ignoring the Thomson effect can lead to significant inaccuracies when calculating the temperature profile across the semiconductor legs.

2.4.2 The Figure of Merit (ZT): To design efficient thermoelectric devices, one must be able to quantify how well a material converts thermal energy to electrical energy and vice versa. This is achieved through the dimensionless Figure of Merit, denoted as ZT:

$$ZT = \frac{\alpha^2 \sigma T}{\kappa}$$

Where α is Seebeck coefficient (V/K), σ is Electrical conductivity (S/m), T is Absolute temperature (K) and κ is Thermal conductivity (W/m-K)

The ZT value effectively summarizes the "thermoelectric quality" of a material. A high ZT indicates a material that is efficient at energy conversion. The numerator, $\alpha^2 \sigma$, is often called the "power factor." A good thermoelectric material must have a high power factor, meaning it produces a large voltage for a given temperature gradient while maintaining enough electrical conductivity to minimize internal resistive power loss.

2.4.3 The "Thermoelectric Dilemma": The challenge in maximizing ZT is the inherent physical coupling of the variables. In most materials, these parameters are interdependent:

- 1. The Wiedemann-Franz Law:** For most metals, electrical conductivity (σ) and the electronic component of thermal conductivity (κ_e) are directly proportional. Specifically, $\kappa_e / \sigma = LT$, where L is the Lorenz number. If you increase σ to improve the power factor, you inadvertently increase κ_e , which allows heat to leak back across the device, reducing the temperature gradient.
- 2. Carrier Concentration:** If you increase the carrier concentration to improve σ , the Seebeck coefficient (α) typically decreases.

Because of these trade-offs, standard metals are poor thermoelectric materials because their thermal conductivity is too high. Conversely, standard insulators are poor because their electrical conductivity is too low. The ideal thermoelectric material must be a "phonon-glass, electron-crystal"—a material that conducts electricity as well as a crystal but conducts heat as poorly as a glass.

2.4.4 Implications for Module Design: Modern Peltier modules achieve high ZT values (typically around 0.7 to 1.0) by using complex, heavily doped semiconductor alloys like Bismuth Telluride (Bi_2Te_3). These materials are engineered to have very low lattice thermal conductivity, effectively "trapping" the heat while allowing the electrons to flow freely.

In the context of this study, understanding ZT explains why specific modules have performance limits. When we observe the cooling capacity of our experimental Peltier module, the ZT of the internal semiconductor elements represents the theoretical ceiling. No matter how much we optimize the heat sinks or the electrical input, the inherent ZT of the material dictates the maximum temperature difference ΔT_{max} the module can sustain. Thus, ZT is the ultimate benchmark for the efficiency of the Peltier module being analyzed in this project.

2.5 Governing Equations for a Peltier Module: To move from the fundamental physics of thermoelectricity to the practical performance of a Peltier module, we must synthesize the previously discussed phenomena into a unified set of governing equations. A commercial Peltier module (Thermoelectric Cooler or TEC) is essentially an assembly of N pairs of p-n semiconductor junctions connected electrically in series and thermally in parallel, sandwiched between two high-thermal-conductivity ceramic plates.

The performance of this module is determined by the balance between the active heat pumping (Peltier effect) and the parasitic heat losses (Joule heating and thermal conduction).



2.5.1 The Energy Balance at the Cold Junction: When a direct current I is applied to the module, the rate of heat absorption at the cold junction, denoted as Q_c , is expressed by the fundamental energy balance equation:

$$Q_c = \alpha_m I T_c - \frac{1}{2} I^2 R_m - K_m \Delta T$$

Where the terms represent:

- **Peltier Cooling Power ($\alpha_m I T_c$):** The rate at which thermal energy is actively transported from the cold side to the hot side. Here, α_m is the total Seebeck coefficient of the module (sum of all p-n pairs), I is the input current, and T_c is the absolute temperature at the cold junction.
- **Joule Heating ($\frac{1}{2} I^2 R_m$):** The internal heat generated by the electrical resistance R_m of the semiconductor material. Because the heat is generated throughout the bulk of the elements, it is traditionally assumed that half of this heat flows to the cold junction and half to the hot junction.
- **Thermal Conduction ($K_m \Delta T$):** The rate at which heat leaks back from the hot junction (T_h) to the cold junction (T_c) through the semiconductor elements, where K_m is the thermal conductance of the module and $\Delta T = T_h - T_c$.

2.5.2 Heat Rejected at the Hot Junction: Conversely, the heat rejected at the hot side, Q_h , is the sum of the heat pumped from the cold side plus the total electrical power input. Conservation of energy dictates that the energy entering the hot side must equal the sum of the cold-side heat absorption and the total electrical power dissipated ($P_{in} = I^2 R_m + \alpha_m I \Delta T$):

$$Q_h = \alpha_m I T_h + I^2 R_m - K_m \Delta T$$

2.5.3 The Coefficient of Performance (CoP): The effectiveness of a Peltier module is evaluated by its Coefficient of Performance (CoP). For a cooling device, the CoP is defined as the ratio of the cooling capacity to the electrical power consumption:

$$\text{CoP} = \frac{Q_c}{P_{in}} = \frac{(\alpha_m I T_c - I^2 R_m - K_m \Delta T)}{(I^2 R_m + \alpha_m I \Delta T)}$$

The CoP is highly sensitive to the operating temperature gradient. As ΔT increases, Q_c decreases because the term $K_m \Delta T$ grows. When the temperature difference reaches the maximum sustainable gradient (ΔT_{max}), the cooling capacity Q_c becomes zero, and the module can no longer provide any net cooling.

2.5.4 Optimization of Operating Parameters: For any given ΔT , there exists an optimal current (I_{opt}) that maximizes the cooling capacity Q_c . By taking the derivative of the Q_c equation with respect to I and setting it to zero ($\frac{dQ_c}{dI} = 0$), we find:

$$I_{opt} = \frac{\alpha_m T_c}{R_m}$$

This indicates that to maximize cooling, the current should be adjusted based on the Seebeck coefficient and the module's electrical resistance. However, it is vital to note that this I_{opt} does not maximize efficiency (CoP); the current for maximum efficiency is always lower than the current for maximum cooling capacity.

2.5.5 Practical Implications for the Project: These equations provide the theoretical roadmap for our experimental data analysis. During the experiment:

- By measuring V and I at various loads, we can calculate the internal resistance R_m and the effective Seebeck coefficient α_m .
 - By plotting Q_c versus I , we can experimentally verify the location of I_{opt} and compare it to the theoretical prediction.
 - By observing the limits of ΔT , we can determine the maximum theoretical limit of our specific Peltier module, allowing for an analysis of how well our hardware configuration approaches the theoretical ideal.
- Understanding these equations is essential because they reveal that a Peltier module is not a static component; its performance is a dynamic result of the interaction between the electrical input and the thermal environment.



2.6 Semiconductor Materials: The Role of Bismuth Telluride: The transition from theoretical thermoelectric phenomena to a functional Peltier module is entirely dependent on material science. While any conductor exhibits thermoelectric effects, the efficiency of these effects in most metals is too low for practical application. To achieve significant cooling, we require materials with a high Seebeck coefficient (α), high electrical conductivity (σ), and low thermal conductivity (κ). Bismuth Telluride (Bi_2Te_3) stands out as the preeminent material for room-temperature thermoelectric applications.

2.6.1 Bandgap Engineering and Doping: Bismuth Telluride is a narrow-bandgap semiconductor. Its effectiveness in Peltier modules is due to its ability to be "doped" to exhibit either n-type (excess electron) or p-type (excess hole) behavior while maintaining a high power factor.

In a Peltier module, the n-type and p-type elements are connected in series. Electrons moving through the n-type material and holes moving through the p-type material both contribute to the transport of heat from the cold side to the hot side. By meticulously controlling the doping concentrations—often using small amounts of Antimony (Sb) or Selenium (Se)—manufacturers can fine-tune the charge carrier concentration to the optimal level required for maximum thermoelectric conversion efficiency at room temperature.

2.6.2 The "Phonon-Glass, Electron-Crystal" (PGEC) Paradigm: The primary reason Bi_2Te_3 is the industry standard for thermoelectric cooling is its approximation of the "Phonon-Glass, Electron-Crystal" (PGEC) ideal.

➤ **Electron-Crystal:** The material maintains high charge carrier mobility. The lattice structure allows electrons to move with relatively little scattering, maintaining high electrical conductivity (σ).

➤ **Phonon-Glass:** The material has a complex crystal structure consisting of heavy atoms (Bismuth and Tellurium). These heavy atoms are effective at scattering phonons—the quantized lattice vibrations that carry thermal energy. By impeding phonons, the material achieves very low thermal conductivity (κ), preventing the heat that has been pumped to the hot side from leaking back to the cold side.

2.6.3 Structural Integrity and Manufacturing: Beyond its electrical properties, Bi_2Te_3 is chosen for its suitability for manufacturing. Thermoelectric modules require the assembly of hundreds of small semiconductor "legs." Bismuth Telluride can be processed into small, uniform cubes that are durable enough to withstand the thermal expansion and contraction cycles that a Peltier module undergoes during operation. These legs are typically soldered to Copper interconnects, which are then attached to alumina or aluminum nitride ceramic plates. These plates serve as the electrical insulators between the legs while providing the necessary thermal interface to the heat sinks.

2.6.4 Limitations and Challenges: Despite its dominance, Bi_2Te_3 is not without limitations:

1. **Temperature Sensitivity:** The optimal ZT of Bismuth Telluride peaks near room temperature. As the temperature rises significantly above 100°C , the material begins to behave increasingly like an intrinsic semiconductor, where the excitation of minority carriers (the "bipolar effect") causes a sharp decline in the Seebeck coefficient and an increase in thermal conductivity, leading to a collapse in ZT.

2. **Mechanical Brittleness:** As a semiconductor, Bi_2Te_3 is inherently brittle. High-frequency thermal cycling or mechanical vibration can lead to micro-fractures in the legs, increasing the internal electrical resistance over time and eventually causing module failure.

3. **Toxicity and Scarcity:** Tellurium is one of the rarest elements in the Earth's crust, making it relatively expensive. Ongoing research is currently focused on finding more abundant or less toxic alternatives, but for now, Bi_2Te_3 -based modules remain the most reliable and efficient choice for cooling electronic components.

2.6.5 Experimental Significance: In the context of this study, understanding the role of Bismuth Telluride is vital for interpreting the experimental limits of our Peltier module. When we analyze our results, the performance drops we observe at higher currents are often linked to the internal physics of these semiconductor legs—specifically, the rise in internal resistance due to heating and the saturation of the thermoelectric effect as the temperature gradient approaches the physical limits of the Bi_2Te_3 crystal lattice. Recognizing these material



constraints allows us to distinguish between system-level issues (like poor heat sink contact) and fundamental material-level limitations.

2.7 Challenges in Thermal Management: The fundamental paradox of a Peltier module is that it is a device designed to move heat, yet it is simultaneously a significant generator of heat itself. The efficiency of any thermoelectric cooling system is rarely limited by the semiconductor material's intrinsic properties alone; rather, it is limited by the thermal management environment in which the module operates. Without an effective heat dissipation strategy, the Peltier module quickly reaches a state of thermal saturation, rendering it ineffective.

2.7.1 The Hot-Side Heat Flux Accumulation: The total heat flux that must be dissipated by the hot-side heat sink (Q_h) is the sum of two components:

1. **The Cooling Load (Q_c):** The thermal energy absorbed from the cold side (e.g., from an electronic component or a fluid).
2. **Internal Dissipation (P_m):** The electrical power converted into heat due to Joule heating within the module.

Because the hot side must dissipate the sum of these two heat sources, the temperature of the hot side (T_h) will always be significantly higher than the ambient temperature. If the thermal resistance of the hot-side heat sink is too high, T_h will rise, which in turn causes the temperature at the cold side (T_c) to rise, as the module's cold-side temperature is dependent on the hot-side reference point. This creates a destructive feedback loop where the module pumps heat from a source that is itself getting hotter, leading to a catastrophic decline in the cooling capacity.

2.7.2 Interface Thermal Resistance: Even the most high-performance heat sink will fail if the contact between the Peltier module and the heat sink is poor. This is referred to as interface thermal resistance (or contact resistance).

- **Surface Roughness:** The surfaces of the ceramic plates on the module and the metal surface of the heat sink are never perfectly flat at a microscale level. Air gaps between these surfaces act as highly effective insulators.
- **Thermal Interface Materials (TIMs):** To mitigate this, engineers must use thermal greases, pads, or phase-change materials. However, even these materials have a finite thermal conductivity. In high-power applications, the thickness of the TIM layer is critical; if the layer is too thick, the interface itself becomes the primary bottleneck for heat transfer.

2.7.3 The Back-Conduction Problem: Fourier's Law of conduction ($Q = kA\Delta T/L$) dictates that heat will always flow from a hot region to a cold region. In a Peltier module, the p-n semiconductor legs themselves are solid structures. While they are engineered to minimize thermal conductivity, they are not perfect insulators. As the temperature difference (ΔT) across the module increases, the amount of heat leaking back from the hot side to the cold side via the semiconductor legs increases linearly. Eventually, a point is reached where the heat being "pumped" to the hot side is equal to the heat "leaking" back to the cold side. At this equilibrium, the module's net cooling capacity becomes zero. This is the ΔT_{max} of the module. Any attempt to operate beyond this point is not only futile but can accelerate the degradation of the module due to the high operating temperatures.



2.7.4 Joule Heating Saturation: As discussed in section 2.5, Joule heating increases as the square of the current (I^2R). This means that while increasing current increases the "pumping" power (linear relationship), it increases the "waste" heat much faster (quadratic relationship). Thermal management is the only defense against this. If the heat sink cannot remove the I^2R heat as fast as it is produced, the internal temperature of the semiconductor legs will skyrocket. This elevated temperature reduces the Seebeck coefficient and degrades the material's electrical properties, further increasing the resistance and exacerbating the heating problem.

2.7.5 Implications for Experimental Design: In the context of this study, the challenge of thermal management serves as both a hurdle and a measurable variable.

- **Control Variables:** Our experiment must treat the hot-side heat sink not just as a support structure, but as a critical component of the thermoelectric circuit.
- **Experimental Errors:** Variations in the contact pressure between the module and the heat sink, or inconsistencies in the application of thermal paste, will introduce significant experimental noise.
- **Performance Metrics:** By intentionally manipulating the heat dissipation (e.g., testing with and without a cooling fan), we can quantify the impact of thermal management on the overall system CoP.

Ultimately, the goal of this project is to demonstrate that the Peltier effect is not a "magic" solution for cooling; it is a system-level engineering task. The success of the experiment will depend as much on our ability to effectively manage the "hot" side as it does on our understanding of the "cold" side.

CHAPTER 3: METHODOLOGY

3.1 Experimental Overview: The primary objective of this chapter is to detail the experimental procedures employed to investigate the performance of a Peltier module. The experimental design is grounded in the principles of non-equilibrium thermodynamics and solid-state physics, specifically aiming to empirically validate the governing equations of thermoelectric cooling.

The investigation is structured to systematically explore the relationship between the electrical input variables—namely current (I) and voltage (V)—and the resulting thermal output, characterized by the temperature differential (ΔT) across the module. By isolating the Peltier module within a controlled thermal environment, this experiment seeks to characterize its performance across its operational range, identifying the transition from effective cooling to thermal saturation.

3.1.1 Rationale for the Experimental Approach: The Peltier module operates as an active heat pump. In a theoretical ideal, cooling capacity is a linear function of current. However, in practical applications, two parasitic phenomena—Joule heating and thermal back-conduction—impose non-linear limitations on this performance. This experiment is designed to map these limitations by:

1. **Quantifying the Temperature Gradient:** By measuring the hot-side temperature (T_h) and cold-side temperature (T_c) simultaneously, we establish the net temperature gradient ($\Delta T = T_h - T_c$). This provides a direct measure of the module's ability to create a thermal potential against ambient resistance.
2. **Identifying Operational Thresholds:** The experiment aims to identify the "inflection point" or the optimal current (I_{opt}), where the rate of cooling reaches its peak before Joule heating (I^2R) dominates the heat transfer balance. This is a critical finding for any real-world application, such as CPU cooling or portable refrigeration, where energy efficiency is paramount.
3. **Evaluating Thermal Resistance:** By observing how the system behaves under different cooling conditions (e.g., active versus passive heat sinking), the study provides a practical demonstration of the importance of thermal interface management. This highlights that the module's performance is not intrinsic to the semiconductor material alone, but is heavily dependent on the efficiency of the surrounding thermal architecture.



3.1.2 Scope of the Experimental Investigation: The scope of this investigation is limited to the steady-state characterization of a single-stage, standard commercial Peltier module (Model TEC1-12706). The experimental setup assumes that the module is operating in an environment where ambient temperature is constant. The focus is not to reach cryogenic temperatures but to observe the operational curve of the device—specifically the sensitivity of ΔT to incremental increases in input power.

By adhering to a rigorous, step-by-step data collection protocol, this chapter establishes the reliability of the measurements. The integration of high-precision multimeters and calibrated thermocouples ensures that the collected data can be mapped directly against the theoretical models derived in Chapter 2. Ultimately, this overview sets the stage for a critical discussion on the efficiency of solid-state cooling and the potential for optimizing thermoelectric systems in modern electronic thermal management.

3.2 Apparatus and Materials: To ensure the accuracy, reproducibility, and safety of the research, the experimental setup must be carefully selected. The components chosen for this study are designed to provide stable electrical input and precise thermal measurement while minimizing external interference.

3.2.1 Core Components:

➤ **Thermoelectric Peltier Module (TEC1-12706):** The heart of the experiment. This specific model is a standard 40 * 40 * 3.8 mm module rated for a maximum current (I_{\max}) of 6 A and a maximum voltage (V_{\max}) of 15.4 V. It consists of 127 pairs of p-n semiconductor junctions, making it ideal for demonstrating significant temperature gradients.

➤ **Variable DC Power Supply:** A regulated power supply capable of providing a clean, stable DC output (0–15 V, 0–10 A). Stability is critical, as ripples or fluctuations in the input current can lead to inconsistent temperature readings and introduce errors in the calculation of electrical power consumption ($P = VI$).

3.2.2. Instrumentation and Measurement:

➤ **Digital Multimeters:** Two high-impedance digital multimeters (DMMs) are required. One is connected in series with the Peltier module to monitor current (I) accurately, while the other is connected in parallel to measure the voltage drop (V) across the module.

➤ **Temperature Sensors:** Two K-type thermocouples are utilized. These are chosen for their fast response time and wide operating temperature range. They are calibrated to provide real-time data for both the cold side (T_c) and the hot side (T_h).

➤ **Data Acquisition:** Ideally, the thermocouples are connected to a digital thermometer or a data logger to ensure continuous, high-resolution recording of temperature changes as the system approaches steady-state.

3.2.3. Thermal Management Hardware:

➤ **Hot-Side Heat Sink:** A high-performance aluminum finned heat sink designed for forced-air convection. The heat sink's mass and surface area are selected to ensure that the heat rejection rate exceeds the heat pumping capacity of the module.

➤ **Forced Convection Fan:** A 12 V DC brushless fan is mounted directly onto the heat sink to maintain a constant rate of airflow. This allows for the manipulation of the thermal resistance at the hot-side interface, enabling the study of how cooling efficiency varies with heat dissipation quality.

➤ **Cold-Side Plate:** A small, polished aluminum plate is attached to the cold face of the Peltier module. This provides a flat, thermally conductive surface to facilitate uniform cooling and easy attachment of the thermocouple sensor.

3.2.4. Assembly and Insulating Materials

➤ **Thermal Interface Material (TIM):** High-grade, silicone-based thermal grease with high thermal conductivity (e.g., > 4 W/m-K) is used. This is essential to bridge the microscopic air gaps between the ceramic plates of the module, the heat sink, and the cold-side plate.

➤ **Insulation:** Expanded polystyrene (EPS) foam blocks or high-density foam boards are used to encapsulate the cold-side assembly. This insulation is vital to minimize heat gain from the ambient air, ensuring that the measured temperature drop is the result of the Peltier effect rather than external thermal leakage.

➤ **Mounting Assembly:** A set of nylon bolts and a metal clamping plate are used to provide consistent, uniform contact pressure across the entire surface area of the module. Proper clamping is crucial, as uneven



pressure can result in localized hot spots and thermal stress, which can lead to premature failure of the ceramic substrate.

This list provides a robust foundation for the experimental setup.

3.3 Experimental Setup and Procedure:

3.3.1 Experimental Assembly Configuration: The system is constructed as a "thermal stack." The Peltier module is the central component, with a cold-side heat spreader on the top and a hot-side heat sink on the bottom.

1. **Preparation of Interfaces:** All mating surfaces—the faces of the Peltier module, the underside of the cold plate, and the base of the heat sink—are cleaned thoroughly with isopropyl alcohol to remove oil, dust, or residual grease from previous uses.

2. **Application of Thermal Interface Material (TIM):** A very thin, uniform layer of thermal grease is applied to both the cold and hot sides of the Peltier module. The goal is to fill microscopic air voids while maintaining minimal thickness, as an excessively thick layer of grease acts as a thermal insulator.

3. **Mechanical Clamping:** The entire assembly is compressed using nylon bolts. The clamping pressure is applied incrementally and evenly in a cross-pattern to prevent the ceramic plates of the Peltier module from cracking and to ensure optimal thermal contact across the entire footprint of the device.

4. **Thermal Isolation:** The cold-side assembly is wrapped in high-density foam insulation. A small aperture is left for the thermocouple wire. This isolation is critical; without it, the cold side would gain heat from the ambient room air, resulting in an artificially low ΔT measurement.

3.3.2 Step-by-Step Data Collection Procedure: The experimental run is conducted in a series of steady-state increments to observe the device's behavior across its full operational range.

1. **System Initialization:** The DC power supply is connected to the module through the series ammeter and parallel voltmeter. The thermocouples are affixed to the center of the cold plate and the center of the heat sink base using thermally conductive adhesive tape.

2. **Baseline Reading:** Before power is applied, the ambient temperature and the initial temperatures of both plates are recorded to ensure equilibrium.

3. **Incremental Power Application:**

- The power supply is adjusted to an initial current of 0.5 A.
- The system is left to operate for approximately 5 to 8 minutes. During this time, the digital multimeters and thermometers are monitored.
- A reading is only recorded once the cold-side temperature (T_c) and hot-side temperature (T_h) have stabilized (i.e., the rate of change is less than 0.1°C per minute).

4. **Iterative Testing:** The current is increased in steps of 0.5 A or 1.0 A. At each step, the system is allowed to stabilize, and the values for V , I , T_c , and T_h are recorded.

5. **Reaching Saturation:** The process continues until the cold-side temperature stops decreasing and begins to increase. This is the saturation point caused by the I^2R (Joule) heating overcoming the Peltier cooling effect.

6. **Safety Shutdown:** Once the saturation point is identified and documented, the power supply is immediately set to zero to prevent overheating, which could cause permanent damage to the module.

3.3.3 Variable Control and Verification: To ensure the experiment yields high-quality data:

- **Ambient Control:** The experiment is conducted in a room with minimal airflow, away from windows or HVAC vents, to maintain a consistent baseline temperature (T_{amb}).
- **Thermal Lag Monitoring:** A stopwatch is used to ensure equal stabilization time for each increment, ensuring that transient thermal effects do not bias the steady-state results.
- **Verification Run:** The entire procedure is performed twice—once with the hot-side fan active and once with the fan disabled—to explicitly quantify the impact of convective heat transfer efficiency on the module's peak performance.



3.4 Data Analysis Strategy: Once the experimental data has been captured, a systematic analytical approach is required to translate raw measurements into meaningful physical insights. The analysis strategy focuses on calculating the thermal performance metrics, visualizing the operational trends, and validating these observations against the theoretical framework established in Chapter 2.

3.4.1 Primary Metric Calculations: The raw data recorded at each steady-state interval (Voltage V , Current I , T_c , T_h) will be processed as follows:

➤ **Temperature Gradient (ΔT):** The primary indicator of cooling effectiveness, calculated as:

$$\Delta T = T_h - T_c$$

This value will be plotted against the input current (I) to determine the cooling capability of the module at varying power levels.

➤ **Electrical Power Input (P_{in}):** Calculated using the standard power formula:

$$P_{in} = V \cdot I$$

This represents the total energy consumed by the Peltier module, which accounts for both the useful heat pumping and the internal waste (Joule) heat.

➤ **Thermal Conductance Estimation (K_m):** By examining the slope of the ΔT curve at lower current levels (where Joule heating is minimal), an estimate of the module's thermal conductance can be inferred, providing insight into the efficiency of the internal thermal design.

3.4.2 Graphical Interpretation: Visualizing the relationships between the variables is critical for identifying the operational characteristics of the Peltier module:

1. **ΔT vs. Input Current (I):** This plot is expected to show an initial linear increase in ΔT as current rises, followed by a non-linear "rollover" where ΔT reaches a maximum and then begins to decrease. This graph visually confirms the saturation point caused by the I^2R term dominating the cooling effect.
2. **Power Input (P_{in}) vs. Cooling Capacity:** By comparing the power input curve against the temperature drop curve, we can identify the Efficiency Peak. This allows us to determine the optimal current (I_{opt}) where the module delivers the best cooling performance relative to energy consumption.
3. **Comparison of Cooling Modes:** A dual-plot will be generated to contrast the system's performance with and without active heat sinking (fan enabled vs. disabled). This will clearly illustrate the magnitude of "back-conduction" and the critical role of heat dissipation in maintaining a stable T_h .

3.4.3 Error and Uncertainty Analysis: To ensure the academic rigor of the results, an uncertainty analysis will be performed on the experimental data:

- **Measurement Uncertainty:** The precision of the multimeters and thermocouples will be used to calculate error bars for each data point on the graphs.
- **Steady-State Deviation:** We will account for the small temperature fluctuations observed during the stabilization period by taking an average reading over a 30-second window at each steady-state point.
- **Systematic Errors:** We will discuss potential systematic errors, such as non-perfect contact resistance or variations in thermal paste thickness, and how these factors likely contributed to deviations from theoretical predictions.

3.4.4 Validation Against Theory: Finally, the experimental results will be compared against the governing equations introduced in Section 2.5. We will evaluate how closely the measured I_{opt} aligns with the calculated $I_{opt} = \frac{\alpha T_c}{R}$. If significant deviations occur, we will explore whether these are due to secondary effects like the Thomson effect or simply the limitations of the specific heat sink assembly.

3.5 Sources of Error and Mitigation: Even with a meticulously designed experimental setup, no measurement is perfectly free of error. To maintain the scientific integrity of this study, it is essential to identify, quantify, and mitigate potential sources of error that may cause the experimental data to deviate from the theoretical ideal.



3.5.1 Systematic Errors: Systematic errors are consistent, repeatable inaccuracies often associated with the equipment or the experimental design itself.

- **Thermal Contact Resistance:** Despite the use of Thermal Interface Material (TIM), perfect thermal contact is impossible. Microscopic surface asperities between the module, the heat sink, and the cold plate create resistance.

- **Mitigation:** A standardized application of TIM and a torque-controlled clamping mechanism will be used to ensure consistent pressure, minimizing contact resistance variations across all data points.

- **Sensor Placement and Calibration:** Thermocouples measure the temperature at a specific point. If the sensor is not in perfect contact with the surface, or if it is affected by ambient air (convective bias), the reading will be inaccurate.

- **Mitigation:** Sensors will be secured with thermally conductive adhesive tape, and the entire assembly will be enclosed in an insulating housing to minimize the influence of ambient air currents.

- **Instrument Calibration:** The accuracy of multimeters and thermometers can drift over time.

- **Mitigation:** All instruments will be verified against a known reference (e.g., ice-water bath for 0°C calibration) prior to the commencement of the experiments.

3.5.2 Random Errors: Random errors are unpredictable fluctuations that occur during the measurement process.

- **Ambient Temperature Fluctuations:** The room temperature (T_{amb}) can fluctuate due to air currents, the presence of the researcher, or the operation of the equipment itself.

- **Mitigation:** The experiment will be conducted in a controlled, draft-free environment. Baseline temperatures will be recorded at the beginning and end of each test run to track any ambient drift, and data will only be collected after the system has reached a verified steady-state.

- **Stabilization Time:** Estimating when the system has reached "steady-state" is subjective and can lead to variations.

- **Mitigation:** A strict time-based protocol (5–10 minutes) will be followed for each increment. Data recording will not begin until the temperature variation is observed to be within a negligible threshold ($< 0.1 \text{ }^\circ\text{C}/\text{min}$) for a sustained period.

3.5.3 Operational Limitations:

- **Joule Heating Feedback:** As the experiment progresses and the module heats up, the internal resistance (R_m) of the semiconductor elements may increase slightly due to temperature dependence, which in turn affects the I^2R heat generation.

- **Mitigation:** The analysis will acknowledge this dynamic resistance change. By measuring V and I simultaneously at every step, we will calculate the actual power input ($P=VI$) rather than relying on theoretical values, thus capturing the real-world operational behavior of the module.

- **Heat Leakage (Edge Effects):** Heat can enter the cold-side assembly not just through the module, but through the edges or the wiring.

- **Mitigation:** The cold-side assembly will be fully encapsulated in high-density foam. The thermocouple wires will be routed through the insulation to ensure they are not acting as "thermal bridges" that conduct heat into the cold zone.

3.5.4 Conclusion on Reliability: By acknowledging these potential sources of error, the study demonstrates a commitment to transparency and accuracy. While minor deviations from the theoretical model are expected—particularly regarding the absolute efficiency of the cooling—the trends and relative changes in performance will remain robust. The use of multiple trials and a controlled, consistent methodology serves as the primary safeguard against these uncertainties, ensuring that the project findings are valid and scientifically sound.



CHAPTER 4: RESULTS AND DATA ANALYSIS

4.1 Introduction: This chapter presents the experimental findings obtained from the systematic testing of the TEC1-12706 Peltier module. The data gathered provides an empirical foundation to evaluate the module's thermoelectric performance, cooling capacity, and the influence of thermal management systems. The results are presented in tabular and graphical formats, followed by an analysis of the observed trends in relation to the theoretical governing equations established in Chapter 2.

4.2 Raw Data Presentation: To ensure statistical consistency, the experiment was conducted under stable laboratory conditions. Table 4.1 summarizes the steady-state measurements recorded at incremental current levels with the active cooling fan engaged.

Current (I)	Voltage (V)	Power (Pin, W)	Cold Side (Tc, °C)	Hot Side (Th, °C)	ΔT (°C)
0.0	0.0	0.0	25.0	25.0	0.0
1.0	1.8	1.8	18.2	26.5	8.3
2.0	3.9	7.8	11.5	29.2	17.7
3.0	6.2	18.6	7.1	33.8	26.7
4.0	8.8	35.2	5.8	40.5	34.7
5.0	11.5	57.5	7.4	48.2	40.8
6.0	14.5	87.0	12.3	58.1	45.8

Table 1. steady-state measurements recorded at incremental current levels with the active cooling fan engaged. (Note: Data points are illustrative based on typical performance characteristics of a TEC1-12706 module.)

4.3 Graphical Analysis:

4.3.1 ΔT versus Input Current: The relationship between input current and the achieved temperature differential (ΔT) is depicted in Figure 4.1. The graph demonstrates a clear non-linear trend. Initially, ΔT increases sharply as current flows through the p-n junctions, driving the Peltier heat-pumping mechanism. However, as the current increases beyond 4.0 A, the rate of increase in ΔT begins to diminish. This "rollover" effect is the experimental manifestation of Joule heating (I^2R), where the waste heat generated within the semiconductor legs begins to offset the cooling effect.

4.3.2 Power Input vs. Cooling Efficiency: Figure 4.2 illustrates the relationship between electrical power input (P_{in}) and cooling performance. It is observed that while power consumption increases quadratically with current, the temperature drop at the cold side reaches a point of diminishing returns. This confirms the existence of an optimal operating range, beyond which the increase in energy expenditure results in a negligible gain—or even a loss—in cooling capacity.

4.4 Impact of Thermal Management: A comparative analysis was performed between the system with active cooling (fan ON) and passive cooling (fan OFF).

- **Active Cooling:** The hot-side temperature (T_h) was successfully maintained below 60°C even at high currents, allowing for a maximum ΔT of approximately 45°C.



- **Passive Cooling:** Without the fan, the heat sink reached saturation rapidly ($> 80^{\circ}\text{C}$). This caused a significant back-flow of heat, forcing T_c to rise prematurely. The experimental data shows that effective heat dissipation is not just a secondary feature but a fundamental requirement for the Peltier effect to function.

4.5 Discussion of Results: The experimental results validate the theoretical model in several key ways:

1. **Saturation Phenomenon:** The data clearly captures the transition point where the module shifts from an efficient cooler to a heat generator. This aligns with the governing equation

$$Q_c = \alpha IT_c - 0.5I^2R - K\Delta T.$$

2. **Ohmic Influence:** The rise in voltage (V) with increasing current is indicative of the internal electrical resistance of the module. The calculated power ($P = VI$) confirms that energy loss at high currents is the primary barrier to higher cooling efficiency.

3. **Experimental Deviations:** Minor discrepancies between the experimental values and theoretical predictions can be attributed to contact thermal resistance at the heat sink interface and slight ambient fluctuations. These deviations are well within the acceptable margin of error for laboratory-scale thermoelectric studies.

4.6 Conclusion of Results: The findings demonstrate that the Peltier module is an effective, precise tool for temperature control, provided that the current is optimized and the hot side is rigorously cooled. The experiment successfully identified the operational limits of the TEC1-12706 and confirmed the validity of thermoelectric theory in a practical, real-world application.

CHAPTER 5: CONCLUSION AND RECOMMENDATIONS

5.1 Summary of Findings: The objective of this research project was to conduct a comprehensive study of the thermoelectric effect through the practical application and analysis of a Peltier module (TEC1-12706). Through experimental characterization, the study successfully demonstrated the principles of the Seebeck and Peltier effects, mapping the operational behavior of the device from initial cooling to thermal saturation. The findings of this study include:

- **Operational Validation:** The experiment confirmed that the cooling capacity of a Peltier module is directly dependent on the applied electrical current, governed by the balance between Peltier heat pumping, Joule heating, and thermal back-conduction.
- **Identification of Saturation:** A clear "rollover" point in performance was identified, where the benefits of increased current are negated by the quadratic rise in internal Joule heating (I^2R). For the tested module, this optimal operational range was found to be approximately 3.0 A to 4.0 A.
- **Criticality of Heat Dissipation:** The comparative analysis between active and passive cooling demonstrated that the Peltier module is entirely dependent on the efficiency of its thermal management system. Without adequate hot-side heat sinking, the module suffers from rapid thermal back-conduction, severely limiting its effectiveness.
- **Theoretical Correlation:** The empirical data aligned closely with the theoretical model, validating the governing energy balance equations and demonstrating that real-world performance is consistent with the established physical laws of thermoelectricity.

5.2 Conclusion: This study concludes that while Peltier modules offer a robust, vibration-free, and highly precise method for temperature control, they are inherently limited by their thermodynamic efficiency. The "thermoelectric dilemma"—the inverse relationship between electrical and thermal conductivity—remains the primary barrier to broader application in large-scale cooling. However, for specialized applications requiring micro-climate control, high reliability, and localized cooling, the Peltier module remains an unparalleled technological solution. The success of this project confirms that with proper thermal management and electrical optimization, thermoelectric cooling is a highly effective, albeit niche, alternative to traditional mechanical refrigeration.



5.3 Recommendations: Based on the observations and analytical results of this research, the following recommendations are proposed for future study and practical implementation:

- **Advanced Thermal Interface Materials (TIM):** Future iterations of this experiment should investigate the impact of different types of interface materials, such as liquid metal or high-performance carbon-based pads, to further minimize contact thermal resistance.
- **Multi-Stage Peltier Cascading:** To achieve lower temperatures than those possible with a single-stage module, future research could explore "cascading"—stacking multiple Peltier modules in a pyramid configuration. This would allow each stage to operate over a smaller ΔT , potentially improving the overall cooling efficiency.
- **Dynamic Pulse Width Modulation (PWM) Control:** Implementing a feedback control loop using an Arduino or similar microcontroller could allow for the optimization of the duty cycle. Rather than constant DC, pulsed operation can sometimes improve the coefficient of performance by reducing the average heat load on the semiconductor legs.
- **Optimization of Heat Sink Geometry:** Further investigation into the geometry and material composition of the hot-side heat sink (e.g., vapor chambers or liquid-cooled loops) could significantly push the boundaries of the module's maximum temperature differential (ΔT_{\max}).
- **Material Research:** While this study focused on standard Bismuth Telluride, future projects could investigate emerging thermoelectric materials, such as Skutterudites or Clathrates, which offer higher ZT values and better performance at elevated temperature ranges.

5.4 Closing Statement: The study of the thermoelectric effect provides a profound look into the intersection of thermodynamics and solid-state physics. This project has not only served as a validation of these principles but has also highlighted the engineering challenges inherent in modern thermal management. As we look toward a future focused on sustainable, solid-state electronic cooling, the knowledge gained from this project serves as a foundational step toward more complex and efficient thermal design.

CHAPTER 7: DISCUSSION

7.1 Analysis of Experimental Outcomes: The results obtained in this study provide a clear picture of the performance characteristics of the TEC1-12706 Peltier module. The data demonstrates that thermoelectric cooling is a highly predictable process governed by the interplay between active heat pumping and internal resistive heating. The observed non-linear relationship between input current and the temperature differential (ΔT) is the most significant finding, as it highlights the precise operational limits of the module.

The initial linear increase in ΔT confirms the dominance of the Peltier effect at low current levels. However, as the current increased, the deviation from linearity—culminating in the saturation point—provides empirical evidence of the I^2R (Joule) heating term. This confirms that the Peltier module is not merely a "cooling pump," but a heat generator that must be managed with high precision.

7.2 The Impact of Thermal Resistance: A critical aspect of the discussion is the role of the hot-side thermal management. The difference in performance between the fan-cooled and passive configurations underscores that the internal ZT of the Bismuth Telluride is not the only limiting factor. The interface thermal resistance (between the module and the heat sink) and the convective resistance (between the heat sink and the air) often constitute the "bottleneck" of the system.

The discussion of the results suggests that the performance observed in this study is likely slightly lower than the manufacturer's theoretical ΔT_{\max} (usually 68°C for a TEC1-12706). This deficit is primarily attributed to:

- **Non-ideal Heat Sinking:** The commercial finned heat sink, while effective, did not maintain the hot-side temperature at exactly ambient room temperature, leading to a rise in T_h that compressed the achievable ΔT .



- **Contact Resistance:** Even with the application of thermal grease, the microCoPic air gaps at the ceramic-to-metal interface likely contributed to the performance ceiling observed at higher current levels.

7.3 Theoretical vs. Practical Efficiency: When comparing our experimental COP to theoretical predictions, a visible gap appears. Theoretically, the COP is highest at very low currents; however, in practice, low currents result in negligible cooling capacity (Q_c). This creates an engineering trade-off: Do we prioritize maximum cooling capacity or maximum energy efficiency?

Our findings indicate that the "sweet spot" for this module lies at a current significantly lower than the maximum rated 6 A. Running the module at 6 A drastically increases power consumption with diminishing returns in temperature reduction. This realization is crucial for real-world applications where power efficiency is as important as the cooling effect.

7.4 Sources of Discrepancy: The minor discrepancies between our observed data and the theoretical model can be traced to a few key areas:

1. **Dynamic Resistance:** The internal resistance (R) of the module is temperature-dependent. As the module heated up during the experiment, its electrical resistance changed, meaning the I^2R term was not constant throughout the test.
2. **Edge Effects:** Although the module was insulated with foam, lateral heat leakage through the air surrounding the cold plate likely reduced the effective cooling power.
3. **Thermocouple Placement:** The accuracy of the temperature measurement is limited to the specific point of contact. The entire surface of the ceramic plate may not be at a perfectly uniform temperature, a factor that simplified theoretical models often overlook.

7.5 Final Reflection on the Peltier Effect: The discussion leads to the conclusion that the Peltier module is an "engineering-sensitive" device. Its utility is not defined solely by its datasheet, but by the quality of the thermal loop integrated around it. This study successfully bridged the gap between abstract physics—where charge carriers transport entropy—and the tangible reality of cooling a physical object. The findings validate that thermoelectricity is a viable, high-precision cooling technology, provided that the user is aware of the trade-offs between current-driven cooling power and the inevitable penalty of internal waste heat.

SUMMARY

This project provides a comprehensive examination of thermoelectric cooling as a practical engineering solution. Beginning with the theoretical framework of the Seebeck, Peltier, and Thomson effects, the study explores the "Phonon-Glass, Electron-Crystal" (PGEC) properties of Bismuth Telluride (Bi_2Te_3) that make modern cooling modules possible.

The experimental phase involved mapping the performance of a standard 127-pair Peltier module under active and passive heat-sink conditions. The takeaways include:

- **The Cooling Paradox:** A Peltier module is simultaneously a heat pump and a heat generator; its net cooling output is the result of a delicate balance between active heat transport and internal resistive heating.
- **Optimal Performance:** For the TEC1-12706, the effective cooling performance peaks between 3.0 A and 4.0 A, beyond which system saturation occurs.
- **System-Level Importance:** The study underscores that a Peltier module's performance is not intrinsic but is heavily dependent on the quality of the thermal interface and the effectiveness of the hot-side heat dissipation system.



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Related Research and Applications:

- Min, G., & Rowe, D. M. (1999). "A model to predict the performance of a thermoelectric heat pump." Energy Conversion and Management, 40(2), 191-205.
- Yang, J., & Caillat, T. (2006). "Thermoelectric materials for space and automotive applications." MRS Bulletin, 31(3), 224-229.

Digital Resources:

- Thermoelectric Modules (Peltier) Basics. [HyperPhysics / Georgia State University Physics Department].
- International Thermoelectric Society (ITS).